

SKKT 71, SKKH 71



SEMIPACK[®] 1

Thyristor / Diode Modules

SKKT 71

SKKH 71

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

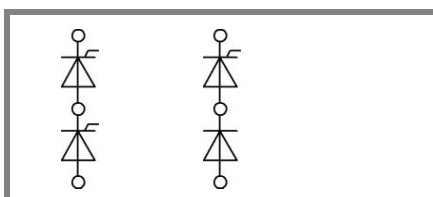
Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 125$ A (maximum value for continuous operation) $I_{TAV} = 70$ A (sin. 180; $T_c = 85$ °C)	
700	600	SKKT 71/06E	
900	800	SKKT 71/08E	SKKH 71/08D
1300	1200	SKKT 71/12E	SKKH 71/12E
1500	1400	SKKT 71/14E	SKKH 71/14E
1700	1600	SKKT 71/16E	SKKH 71/16E
1900	1800	SKKT 71/18E	SKKH 71/18E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	70 (50)	A
I_D	P3/180; $T_a = 45$ °C; B2 / B6	62 / 75	A
	P3/180F; $T_a = 35$ °C; B2 / B6	115 / 145	A
I_{RMS}	P3/180F; $T_a = 45$ °C; W1 / W3	155 / 3 * 115	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms	1600	A
	$T_{vj} = 125$ °C; 10 ms	1450	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	13000	A ² s
	$T_{vj} = 125$ °C; 8,3 ... 10 ms	10500	A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 300$ A	max. 1,9	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 0,9	V
r_T	$T_{vj} = 125$ °C	max. 3,5	mΩ
I_{DD}, I_{RD}	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 20	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	1	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 150	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C; SKK ...D / SKK ...E	max. 500 / 1000	V/μs
t_q	$T_{vj} = 125$ °C,	80	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 250	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 600	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 3	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	max. 6	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,35 / 0,18	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,37 / 0,19	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,39 / 0,2	K/W
$R_{th(c-s)}$	per thyristor / per module	0,2 / 0,1	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 % ¹⁾	Nm
M_t	to terminals	3 ± 15 %	Nm
a		5 * 9,81	m/s ²
m	approx.	95	g
Case	SKKT	A 5	
	SKKH	A 6	



SKKT

SKKH

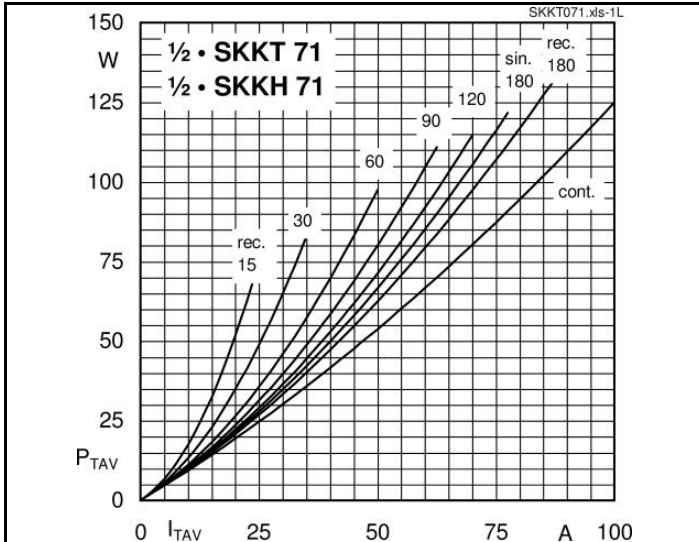


Fig. 1L Power dissipation per thyristor vs. on-state current

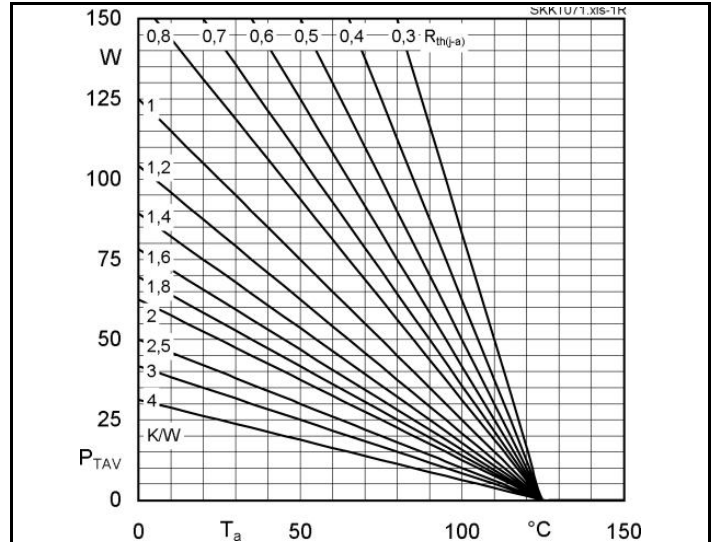


Fig. 1R Power dissipation per thyristor vs. ambient temp.

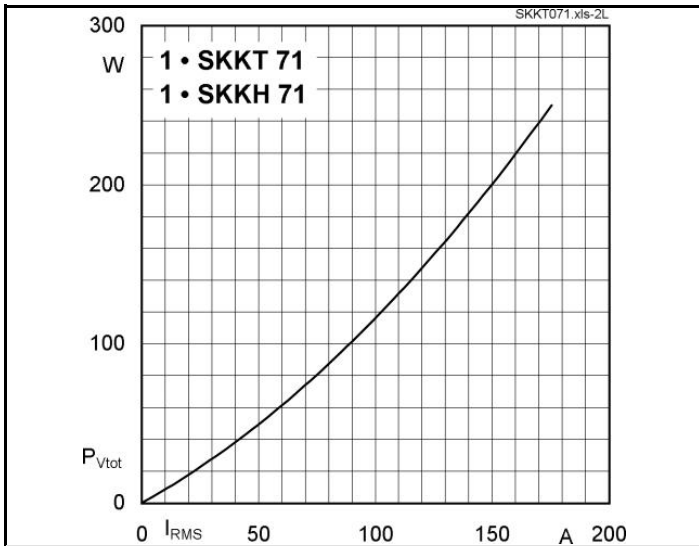


Fig. 2L Power dissipation per module vs. rms current

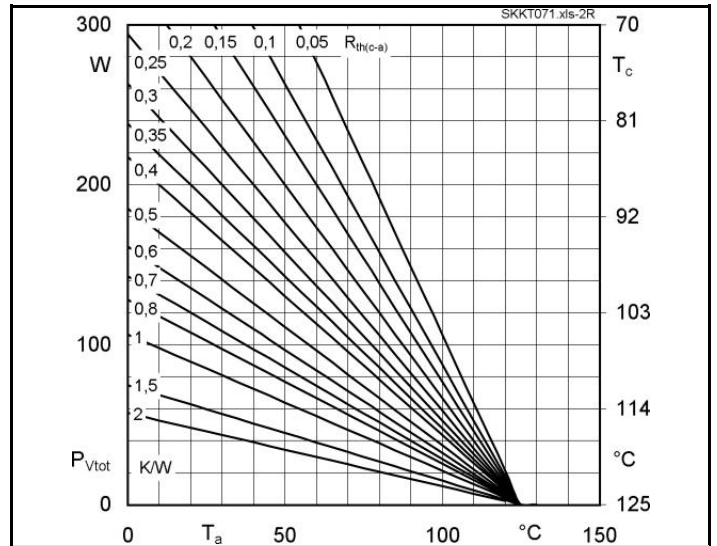


Fig. 2R Power dissipation per module vs. case temp.

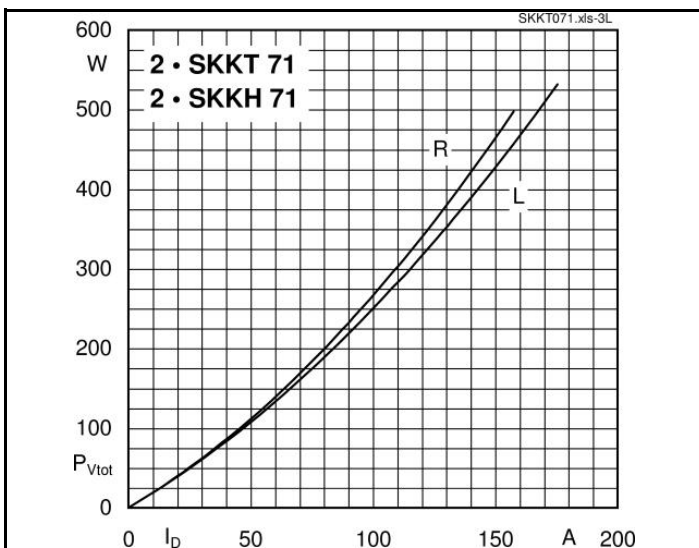


Fig. 3L Power dissipation of two modules vs. direct current

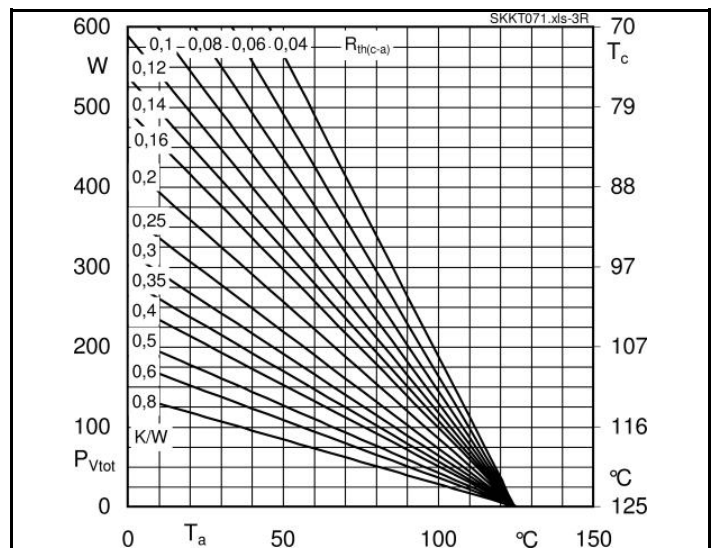
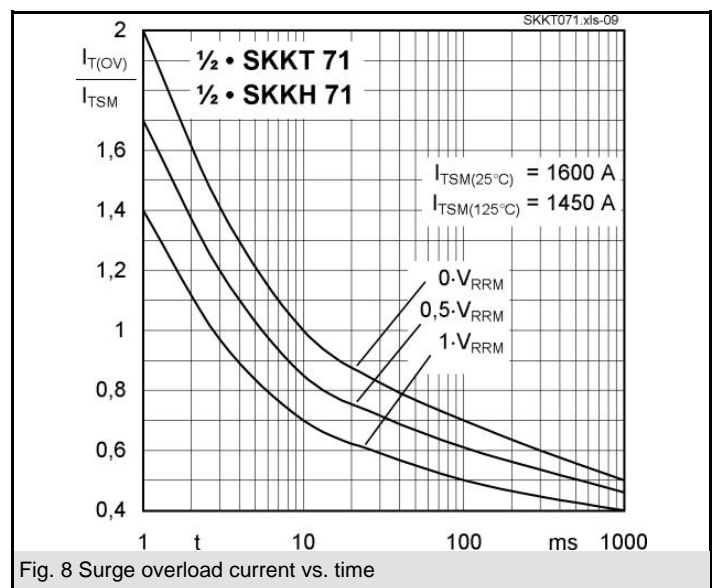
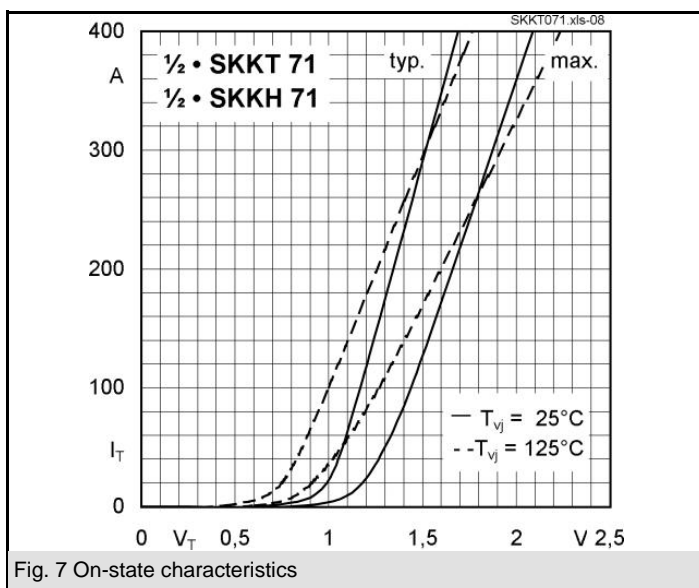
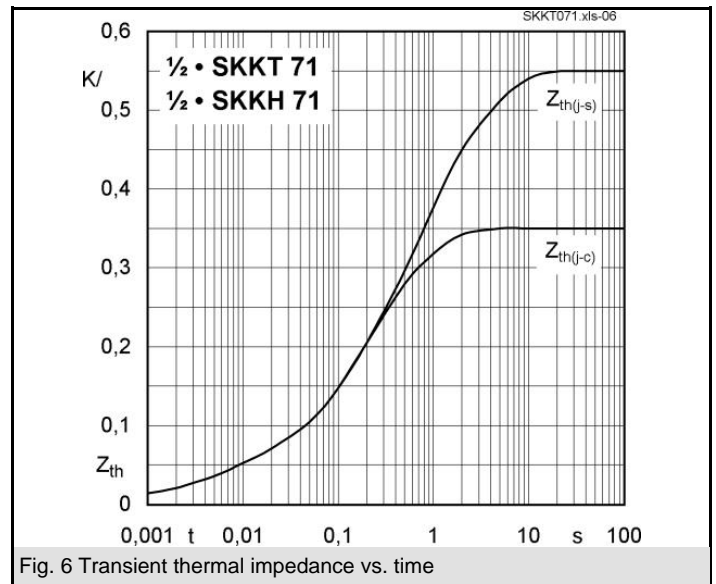
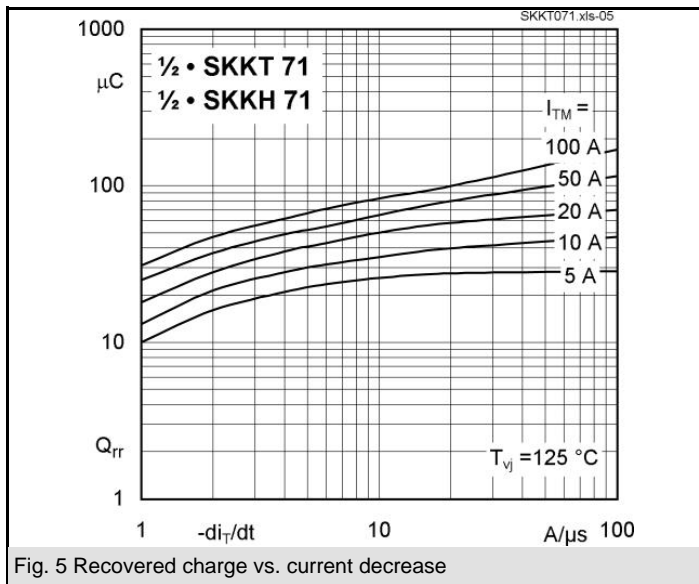
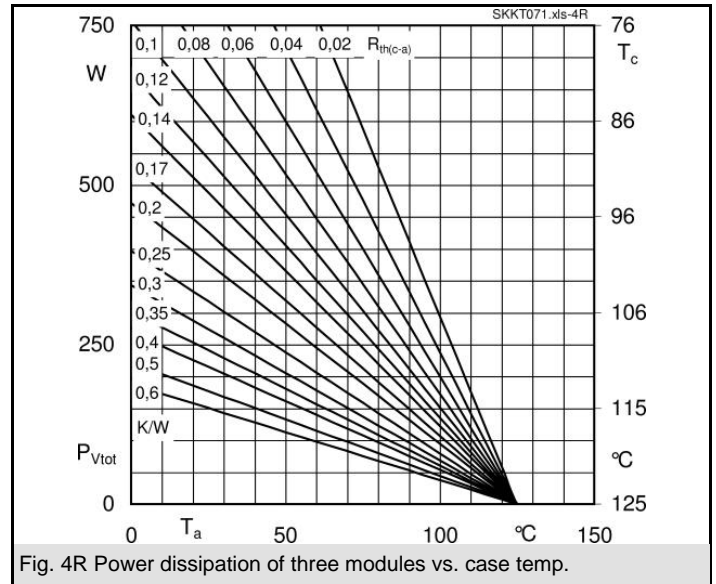
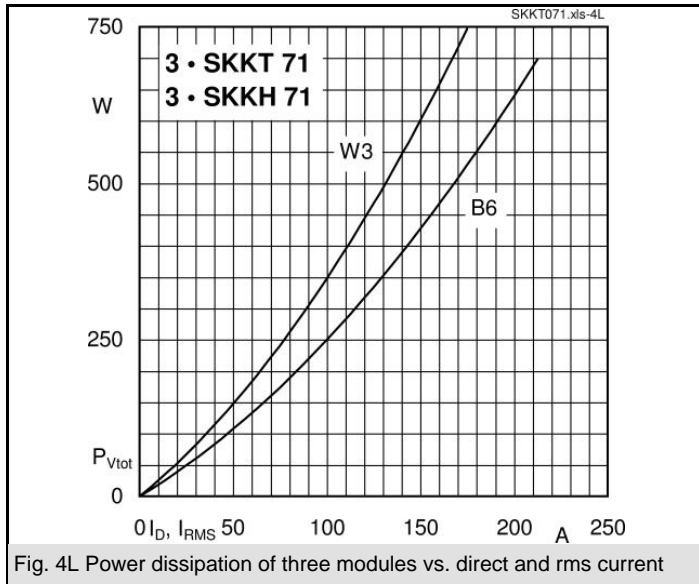


Fig. 3R Power dissipation of two modules vs. case temp.

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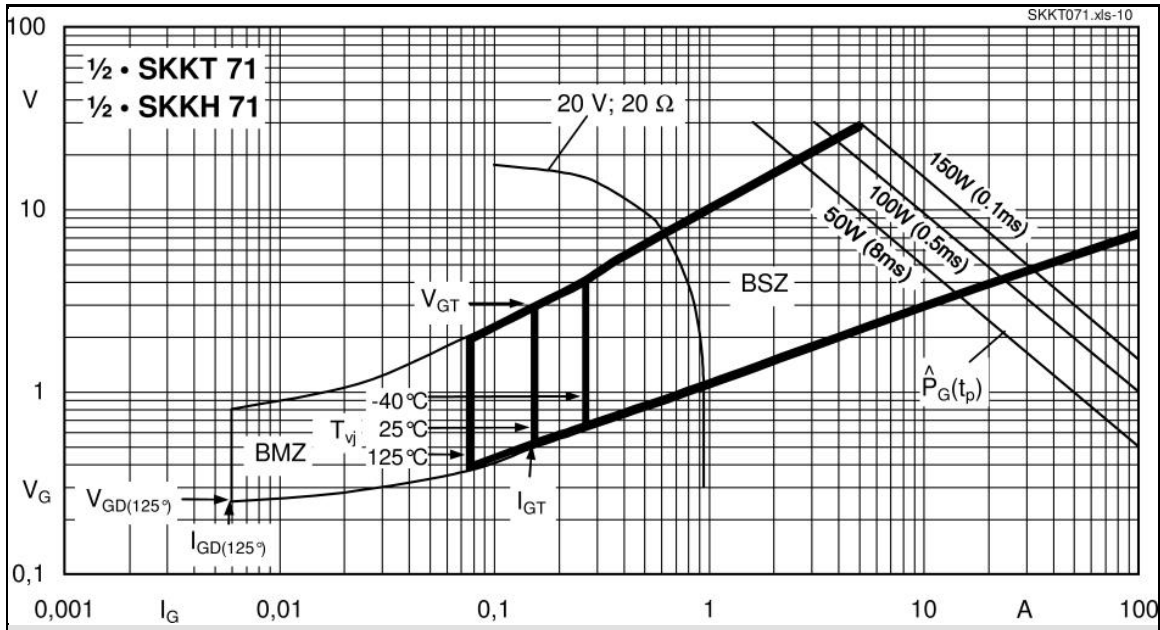
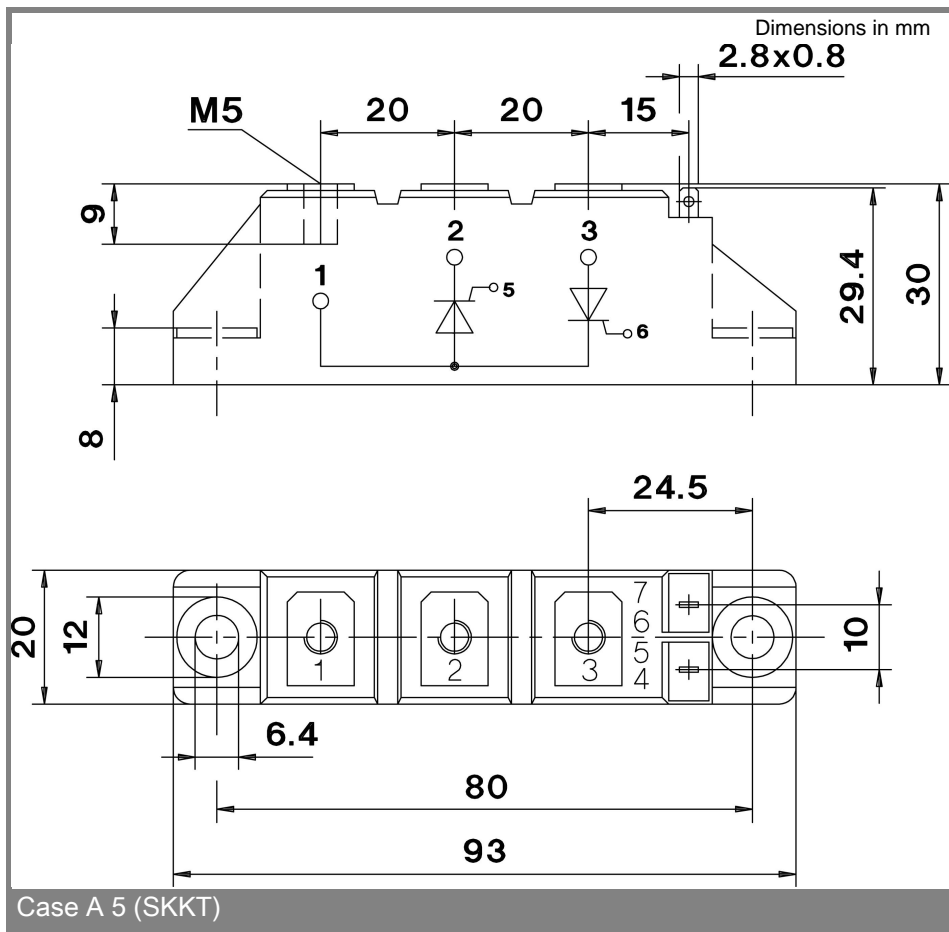
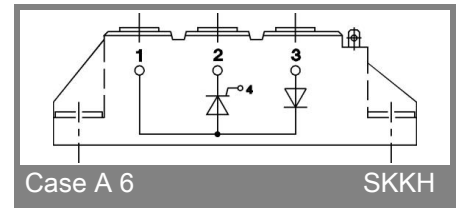


Fig. 9 Gate trigger characteristics



Case A 5 (SKKT)



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